EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	("20030080384").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L2	212229	silicon adj carbide or "SiC"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L3	5830	L2 and (pressure with "Pa")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L4	1369	L3 and carbon with ((silicon adj carbide) or "SiC")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L5	1286	L4 and temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L6	14	L5 and silicon adj carbide with carbon adj layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L7	1	L6 and activat$3 with anneal$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L8	4	("20030052321" | "6270573").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09

L9	1369	L4 and carbon	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L10	2	L8 and carbon	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L11	503	(silicon adj carbide with impurity) and ((heat$3 or anneal$3) with carbon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L12	70	(silicon adj carbide with impurity) and ((heat$3 or anneal$3) with carbon with pressure)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L13	1	L12 and activat$3 with impurity	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L14	1	L12 and (second adj (heat $3 or anneal$3)) same pressure	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L15	491	(silicon adj carbide with (implant$3 or dop$3)) and ((heat$3 or anneal$3) with carbon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L16	139	(silicon adj carbide with (implant$3 or dop$3)) and ((heat$3 or anneal$3) with carbon with surface)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L17	8	L16 and ((second or higher or lower) adj pressure)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09

L18	17	(silicon adj carbide with (implant$3 or dop$3)) and (((heat$3 or anneal $3) with carbon with surface) same vacuum)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L19	204740	heat$3 with silicon adj carbide with form$3 carbon with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L20	34	L19 and (implant$3 with impurity with silicon adj carbide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L21	23	L20 and activat$3 with impurities	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L22	23	L21 and (heat$3 with silicon adj carbide with form$3 carbon with surface)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L23	524	438/570.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L24	1379	438/758.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L25	925	438/268.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L26	0	L23 and (silicon adj carbide with impurity) and ((heat$3 or anneal$3) with carbon with pressure)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09

L27	0	L24 and (silicon adj carbide with impurity) and ((heat$3 or anneal$3) with carbon with pressure)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L28	0	L25 and (silicon adj carbide with impurity) and ((heat$3 or anneal$3) with carbon with pressure)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L29	0	L23 and (silicon adj carbide with impurity) and ((heat$3 or anneal$3) with carbon same pressure)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L30	0	L24 and (silicon adj carbide with impurity) and ((heat$3 or anneal$3) with carbon same pressure)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L31	1	L25 and (silicon adj carbide with impurity) and ((heat$3 or anneal$3) with carbon same pressure)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L32	201094	L23 and heat$3 with silicon adj carbide with form$3 carbon with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L33	201093	L24 and heat$3 with silicon adj carbide with form$3 carbon with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L34	201095	L25 and heat$3 with silicon adj carbide with form$3 carbon with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L35	0	L24 and heat$3 with silicon adj carbide with form$3 adj carbon with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09

L36	1	L24 and heat$3 with silicon adj carbide with form$3 with carbon with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L37	0	L23 and heat$3 with silicon adj carbide with form$3 with carbon with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L38	2	L25 and heat$3 with silicon adj carbide with form$3 with carbon with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L39	2	L25 and (heat$3 or anneal $3) with ((silicon adj carbide) or "SiC") with (form$3 or deposit$3) with carbon with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L40	1	L24 and (heat$3 or anneal $3) with ((silicon adj carbide) or "SiC") with (form$3 or deposit$3) with carbon with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L41	0	L23 and (heat$3 or anneal $3) with ((silicon adj carbide) or "SiC") with (form$3 or deposit$3) with carbon with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L42	0	L23 and (heat$3 or anneal $3) with ((silicon adj carbide) or "SiC") with (form$3 or deposit$3) with carbon same pressure	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L43	0	L24 and (heat$3 or anneal $3) with ((silicon adj carbide) or "SiC") with (form$3 or deposit$3) with carbon same pressure	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L44	0	L25 and (heat$3 or anneal $3) with ((silicon adj carbide) or "SiC") with (form$3 or deposit$3) with carbon same pressure	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09

L45	0	L25 and (heat$3 or anneal $3) with ((silicon adj carbide) or "SiC") with (form$3 or deposit$3) with carbon same vacuum	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L46	235	(heat$3 or anneal$3) with ((silicon adj carbide) or "SiC") with (form$3 or deposit$3) with carbon same pressure	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L47	9	(heat$3 or anneal$3) with ((silicon adj carbide) or "SiC") with (form$3 or deposit$3) with carbon same low adj pressure	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L48	2	L46 and activat$3 with anneal$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L49	1	L46 and activat$3 with impurities	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L50	38	L46 and activat$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L51	1	L46 and activat$3 with (dopant or impurit$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L52	3	L46 and activat$3 with (nitrogen)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09

L53	397394	L1 L2 L3 L4 L5 L6 L7 L8 L9 L10 L11 L12 L13 L14 L15 L16 L17 L18 L19 L20 L21 L22 L23 L24 L25 L26 L27 L28 L29 L30 L31 L32 L33 L34 L35 L36 L37 L38 L39 L40 L41 L42 L43 L44 L45 L46 L47 L48 L49 L50 L51 L52	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:09
L54	404	(heat$3 with silicon adj carbide with form$3 with (carbon or diamond or graphite) with surface)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:14
L55	1	51 and activat$3 with (dopant or impurit$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:15
L56	1493	(heat$3 with silicon adj carbide with form$3 with (carbon or diamond or graphite))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:17
L57	296	(heat$3 or anneal$3) with ((silicon adj carbide) or "SiC") with (form$3 or deposit$3) with (carbon or diamond or graphite) same pressure	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:17
L58	8	57 and activat$3 with (dopant or ion or impurit $3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:18
L59	35	56 and activat$3 with (dopant or ion or impurit $3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:20
L60	3	"2001-068428"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:30

L61	4	"2001068428"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:30
L62	93723	"Denso"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:37
L63	2207	62 and carbon	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:38
L64	159	63 and silicon adj carbide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:38
L65	92800	Denso.AS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:40
L66	2207	63 and carbon	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:40
L67	159	64 and silicon adj carbide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:40
L68	17	67 and activat$3 with (dopant or ion or impurit $3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:40
S1	2	("20030080384").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 20:31

S2	212229	silicon adj carbide or "SiC"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 20:44
S3	5830	S2 and (pressure with "Pa")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 20:44
S4	1369	S3 and carbon with ((silicon adj carbide) or "SiC")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 20:45
S5	1286	S4 and temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 20:45
S6	14	S5 and silicon adj carbide with carbon adj layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 20:45
S7	1	S6 and activat$3 with anneal$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 20:46
S8	4	("20030052321" | "6270573").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 20:52
S9	1369	S4 and carbon	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:03
S10	2	S8 and carbon	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:03

S11	503	(silicon adj carbide with impurity) and ((heat$3 or anneal$3) with carbon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:05
S12	70	(silicon adj carbide with impurity) and ((heat$3 or anneal$3) with carbon with pressure)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:05
S13	1	S12 and activat$3 with impurity	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:06
S14	1	S12 and (second adj (heat $3 or anneal$3)) same pressure	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:06
S15	491	(silicon adj carbide with (implant$3 or dop$3)) and ((heat$3 or anneal$3) with carbon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:10
S16	139	(silicon adj carbide with (implant$3 or dop$3)) and ((heat$3 or anneal$3) with carbon with surface)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:10
S17	8	S16 and ((second or higher or lower) adj pressure)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:11
S18	17	(silicon adj carbide with (implant$3 or dop$3)) and (((heat$3 or anneal $3) with carbon with surface) same vacuum)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:19
S19	204740	heat$3 with silicon adj carbide with form$3 carbon with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:28

S20	34	S19 and (implant$3 with impurity with silicon adj carbide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:29
S21	23	S20 and activat$3 with impurities	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:29
S22	23	S21 and (heat$3 with silicon adj carbide with form$3 carbon with surface)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:31
S23	524	438/570.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:50
S24	1379	438/758.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:50
S25	925	438/268.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:50
S26	0	S23 and (silicon adj carbide with impurity) and ((heat$3 or anneal$3) with carbon with pressure)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:51
S27	0	S24 and (silicon adj carbide with impurity) and ((heat$3 or anneal$3) with carbon with pressure)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:51
S28	0	S25 and (silicon adj carbide with impurity) and ((heat$3 or anneal$3) with carbon with pressure)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:51

S29	0	S23 and (silicon adj carbide with impurity) and ((heat$3 or anneal$3) with carbon same pressure)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:51
S30	0	S24 and (silicon adj carbide with impurity) and ((heat$3 or anneal$3) with carbon same pressure)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:52
S31	1	S25 and (silicon adj carbide with impurity) and ((heat$3 or anneal$3) with carbon same pressure)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:52
S32	201094	S23 and heat$3 with silicon adj carbide with form$3 carbon with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:52
S33	201093	S24 and heat$3 with silicon adj carbide with form$3 carbon with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:53
S34	201095	S25 and heat$3 with silicon adj carbide with form$3 carbon with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:54
S35	0	S24 and heat$3 with silicon adj carbide with form$3 adj carbon with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:55
S36	1	S24 and heat$3 with silicon adj carbide with form$3 with carbon with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:56
S37	0	S23 and heat$3 with silicon adj carbide with form$3 with carbon with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:56

S38	2	S25 and heat$3 with silicon adj carbide with form$3 with carbon with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 21:56
S39	2	S25 and (heat$3 or anneal $3) with ((silicon adj carbide) or "SiC") with (form$3 or deposit$3) with carbon with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 22:00
S40	1	S24 and (heat$3 or anneal $3) with ((silicon adj carbide) or "SiC") with (form$3 or deposit$3) with carbon with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 22:00
S41	0	S23 and (heat$3 or anneal $3) with ((silicon adj carbide) or "SiC") with (form$3 or deposit$3) with carbon with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 22:00
S42	0	S23 and (heat$3 or anneal $3) with ((silicon adj carbide) or "SiC") with (form$3 or deposit$3) with carbon same pressure	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 22:00
S43	0	S24 and (heat$3 or anneal $3) with ((silicon adj carbide) or "SiC") with (form$3 or deposit$3) with carbon same pressure	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 22:01
S44	0	S25 and (heat$3 or anneal $3) with ((silicon adj carbide) or "SiC") with (form$3 or deposit$3) with carbon same pressure	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 22:02
S45	0	S25 and (heat$3 or anneal $3) with ((silicon adj carbide) or "SiC") with (form$3 or deposit$3) with carbon same vacuum	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 22:02

S46	235	(heat$3 or anneal$3) with ((silicon adj carbide) or "SiC") with (form$3 or deposit$3) with carbon same pressure	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 22:02
S47	9	(heat$3 or anneal$3) with ((silicon adj carbide) or "SiC") with (form$3 or deposit$3) with carbon same low adj pressure	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 22:03
S48	2	S46 and activat$3 with anneal$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 22:04
S49	1	S46 and activat$3 with impurities	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 22:04
S50	38	S46 and activat$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 22:04
S51	1	S46 and activat$3 with (dopant or impurit$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 22:07
S52	3	S46 and activat$3 with (nitrogen)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/15 22:07

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